

Single P-channel MOSFET

ELM34419AA-N

■ General description

ELM34419AA-N uses advanced trench technology to provide excellent $R_{ds(on)}$, low gate charge and low gate resistance.

■ Features

- $V_{ds} = -30V$
- $I_d = -10A$
- $R_{ds(on)} < 20m\Omega$ ($V_{gs} = -10V$)
- $R_{ds(on)} < 35m\Omega$ ($V_{gs} = -4.5V$)

■ Maximum absolute ratings

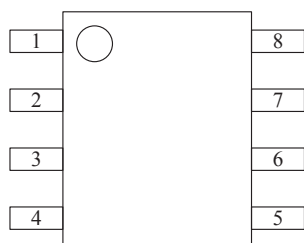
Parameter	Symbol	Limit	Unit	Note
Drain-source voltage	V_{ds}	-30	V	
Gate-source voltage	V_{gs}	± 25	V	
Continuous drain current	I_d	$T_a = 25^\circ C$	-10	A
		$T_a = 70^\circ C$	-8	
Pulsed drain current	I_{dm}	-55	A	3
Avalanche current	I_{ar}	-29	A	
Avalanche energy	E_{as}	43	mJ	
Power dissipation	P_d	$T_a = 25^\circ C$	3	W
		$T_a = 70^\circ C$	2	
Junction and storage temperature range	T_j, T_{stg}	-55 to 150	$^\circ C$	

■ Thermal characteristics

Parameter	Symbol	Typ.	Max.	Unit	Note
Maximum junction-to-case	$R_{\theta jc}$		25	$^\circ C/W$	
Maximum junction-to-ambient	$R_{\theta ja}$		40	$^\circ C/W$	

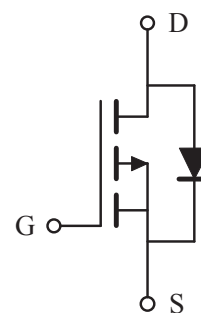
■ Pin configuration

SOP-8(TOP VIEW)



Pin No.	Pin name
1	SOURCE
2	SOURCE
3	SOURCE
4	GATE
5	DRAIN
6	DRAIN
7	DRAIN
8	DRAIN

■ Circuit



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■Electrical characteristics

Ta=25°C

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit	Note
STATIC PARAMETERS							
Drain-source breakdown voltage	BV _{dss}	I _d =-250μA, V _{gs} =0V	-30			V	
Zero gate voltage drain current	I _{dss}	V _{ds} =-24V, V _{gs} =0V			-1	μA	
		V _{ds} =-20V, V _{gs} =0V, T _j =125°C			-10		
Gate-body leakage current	I _{gss}	V _{ds} =0V, V _{gs} =±25V			±100	nA	
Gate threshold voltage	V _{gs(th)}	V _{ds} =V _{gs} , I _d =-250μA	-1.0	-1.5	-3.0	V	
Static drain-source on-resistance	R _{ds(on)}	V _{gs} =-10V, I _d =-10A		15	20	mΩ	1
		V _{gs} =-4.5V, I _d =-7A		25	35	mΩ	
Forward transconductance	G _{fs}	V _{ds} =-10V, I _d =-10A		24		S	1
Diode forward voltage	V _{sd}	I _s =-1A, V _{gs} =0V			-1.2	V	1
Max. body-diode continuous current	I _s				-2.5	A	
DYNAMIC PARAMETERS							
Input capacitance	C _{iss}			1490		pF	
Output capacitance	C _{oss}	V _{gs} =0V, V _{ds} =-15V, f=1MHz		301		pF	
Reverse transfer capacitance	C _{rss}			190		pF	
Gate resistance	R _g	V _{gs} =15mV, V _{ds} =0V, f=1MHz		7.8	9.0	Ω	
SWITCHING PARAMETERS							
Total gate charge	Q _g	V _{gs} =-10V, V _{ds} =-15V I _d =-10A		26		nC	2
Gate-source charge	Q _{gs}			4		nC	2
Gate-drain charge	Q _{gd}			5		nC	2
Turn-on delay time	t _{d(on)}	V _{gs} =-10V, V _{ds} =-15V I _d ≈-1A, R _{gen} =6Ω		5.7		ns	2
Turn-on rise time	t _r			10.0		ns	2
Turn-off delay time	t _{d(off)}			18.0		ns	2
Turn-off fall time	t _f			5.0		ns	2

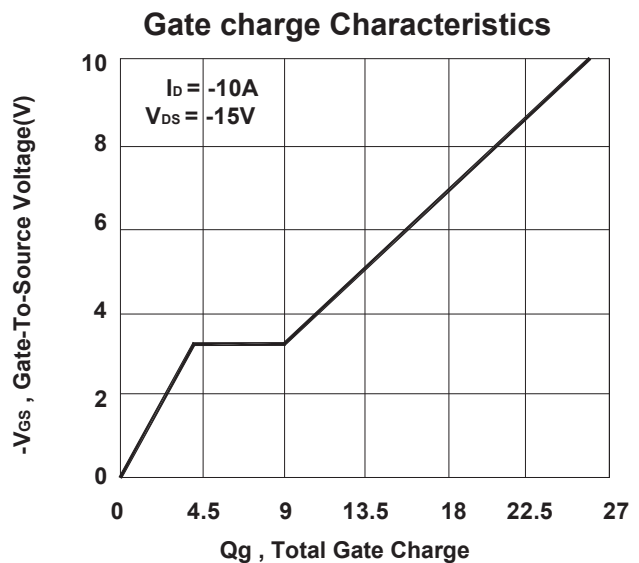
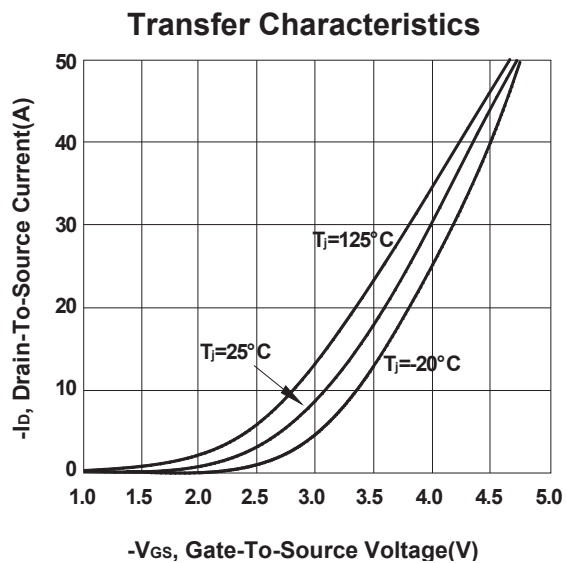
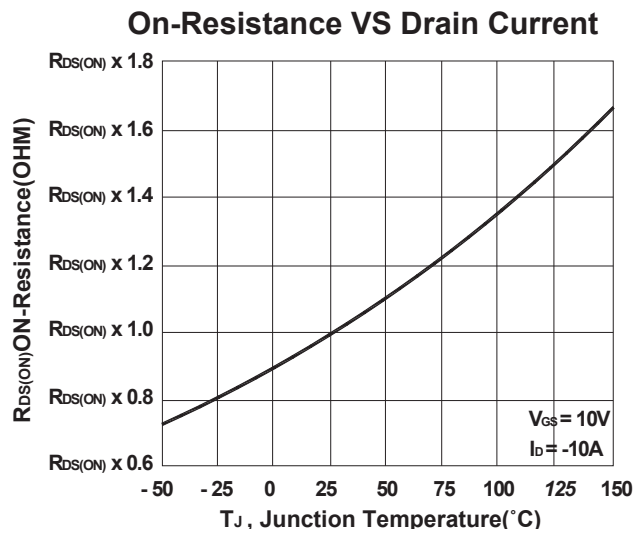
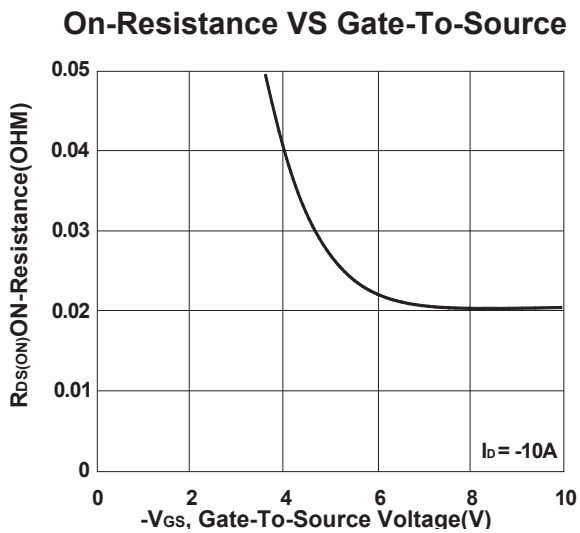
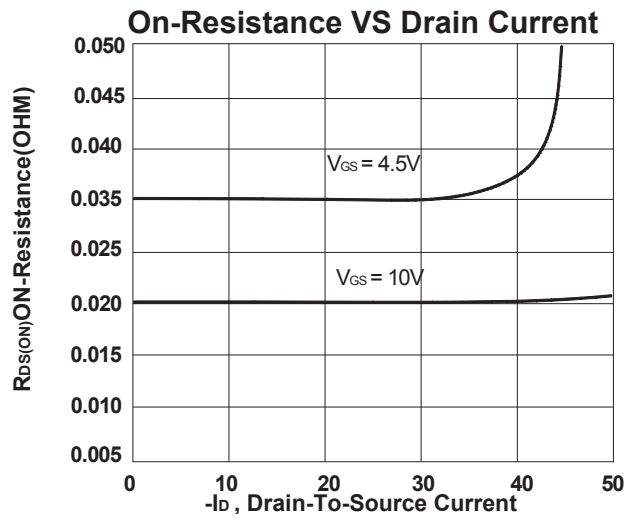
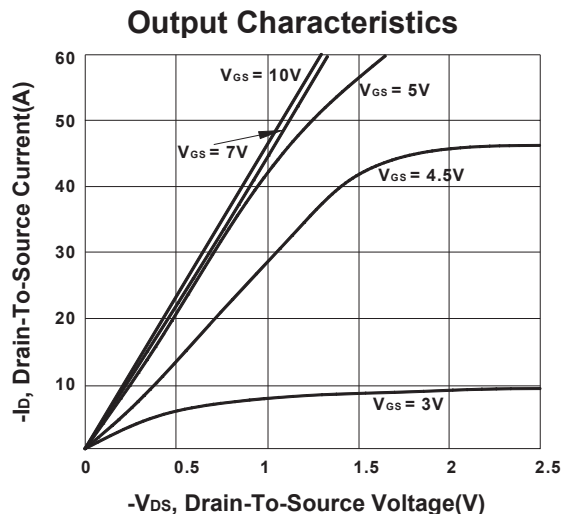
NOTE :

1. Pulsed width ≤ 300μsec and Duty cycle ≤ 2%.
2. Independent of operating temperature.
3. Pulsed width limited by maximum junction temperature.
4. Duty cycle ≤ 1%.

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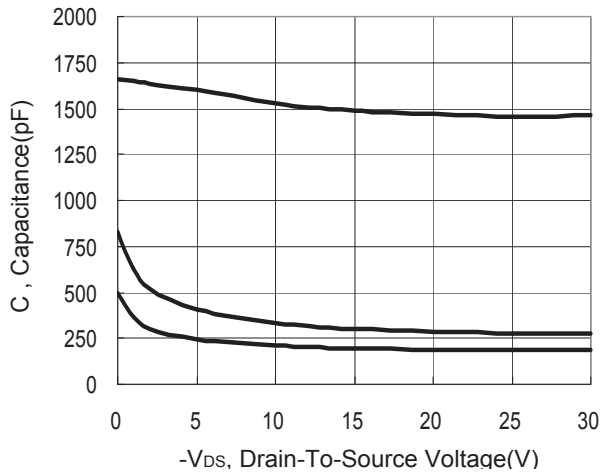
■ Typical electrical and thermal characteristics



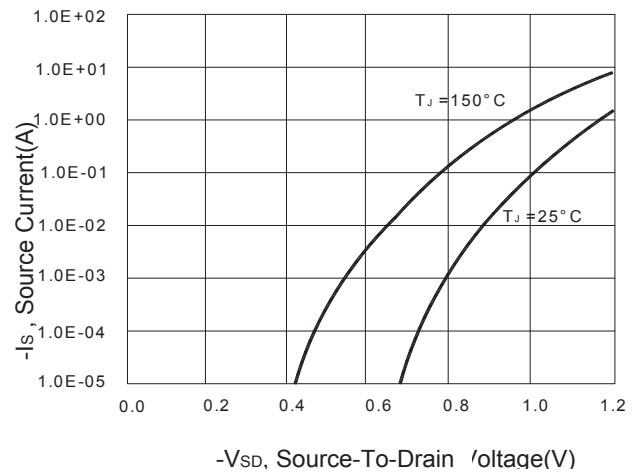
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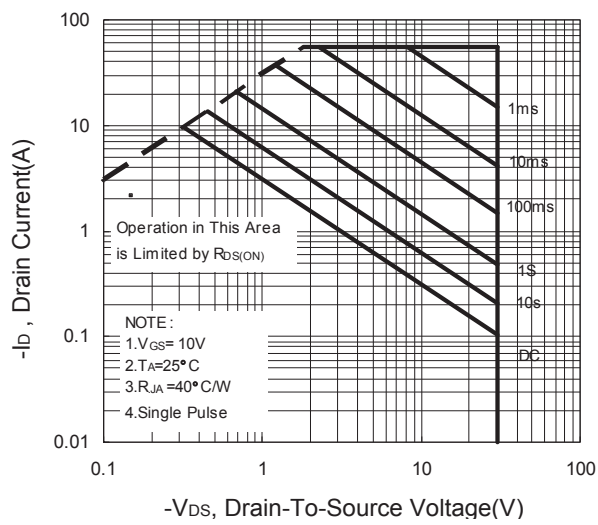
Capacitance Characteristic



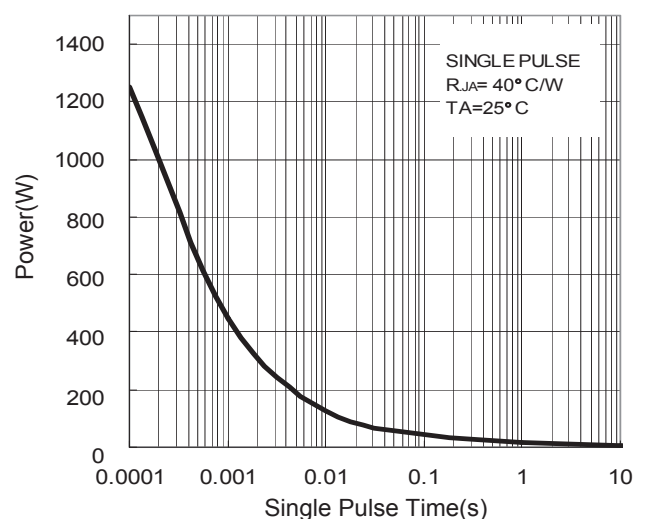
Body Diode Forward Voltage



Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve

